



LOW VOLTAGE 0.5Ω MAX QUAD SPDT SWITCH WITH BREAK BEFORE MAKE FEATURE

- HIGH SPEED:
 - t_{PD} = 0.3ns (TYP.) at V_{CC} = 3.0V t_{PD} = 0.4ns (TYP.) at V_{CC} = 2.3V
- ULTRA LOW POWER DISSIPATION: $I_{CC} = 0.2\mu A \text{ (MAX.)}$ at $T_A = 85^{\circ}C$
- LOW "ON" RESISTANCE V_{IN} =0V: $R_{ON} = 0.5\Omega$ (MAX. $T_{A} = 25$ °C) at $V_{CC} = 2.7$ V $R_{ON} = 0.8\Omega$ (MAX. $T_{A} = 25$ °C) at $V_{CC} = 2.3$ V $R_{ON} = 3.0\Omega$ (MAX. $T_{A} = 25$ °C) at $V_{CC} = 1.8$ V
- WIDE OPERATING VOLTAGE RANGE: V_{CC} (OPR) = 1.65V to 4.3V SINGLE SUPPLY
- 4.3V TOLERANT AND 1.8V COMPATIBLE THRESHOLD ON DIGITAL CONTROL INPUT at V_{CC} = 2.3 to 3.0V
- LATCH-UP PERFORMANCE EXCEEDS 300mA (JESD 17)
- ESD PERFORM. (ANALOG CHAN. vs GND):
 HBM > 7KV (MIL STD 883 method 3015)

DESCRIPTION

The STG3699 is an high-speed CMOS LOW VOLTAGE QUAD ANALOG S.P.D.T. (Single Pole Dual Throw) SWITCH or 2:1 Multiplexer/ Demultiplexer Switch fabricated in silicon gate C²MOS technology. It is designed to operate from 1.65V to 4.3V, making this device ideal for portable applications.

It offers very low ON-Resistance (<0.5 Ω) at V_{CC}=3.0V. The nIN inputs are provided to control the switches. The switches nS1 are ON (they are

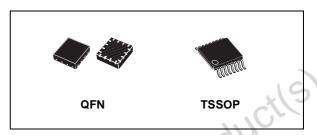
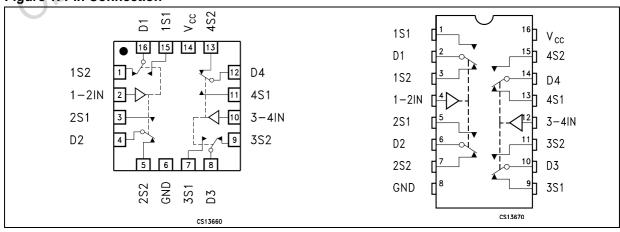


Table 1: Order Codes

PACKAGE	T & R
TSSOP	STG3699TTR
QFN	STG3699QTR

connected to common Ports Dn) when the nIN input is held high and OFF (high impedance state exists between the two ports) when nIN is held low; the switches nS2 are ON (they are connected to common Ports Dn) when the nIN input is held low and OFF (high impedance state exists between the two ports) when IN is held high. Additional key features are fast switching speed, Break Before Make Delay Time and Ultra Low Power Consumption. All inputs and outputs are equipped with protection circuits against static discharge, giving them ESD immunity and transient excess voltage. It's available in the commercial temperature range in TSSOP and QFN3x3mm package.

Figure 1: Pin Connection



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Figure 2: Input Equivalent Circuit

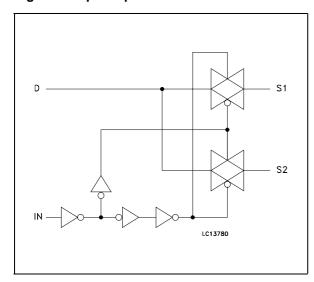


Table 2: Pin Description

TSSOP ⁽¹⁾ PIN N°	QFN ⁽¹⁾ PIN N°	SYMBOL	NAME AND FUNCTION
1, 5, 9, 13, 3, 7, 11, 15	15, 3, 7, 11, 1, 5, 9, 13	1S1 to 4S1, 1S2 to 4S2	Independent Channels
2, 6, 10, 14	16, 4, 8, 12	D1 to D4	Common Channels
4, 12	2, 10	1-2IN, 3-4IN	Controls
16	14 V _{CC}		Positive Sup- ply Voltage
8	6	GND	Ground (0V)

Exposed pad must be soldered to a floating plane. Do NOT connect to power or ground.

Table 3: Truth Table

IN	SWITCH S1	SWITCH S2
Н	ON	OFF ⁽¹⁾
L	OFF ⁽¹⁾	ON

^{1.} High Impedance

Table 4: Absolute Maximum Ratings

Symbol	Parameter		Value	Unit
V _{CC}	Supply Voltage	70-	-0.5 to 4.6	V
V _I	DC Input Voltage	0.	-0.5 to V _{CC} + 0.5	V
V _{IC}	DC Control Input Voltage		-0.5 to 4.6	V
Vo	DC Output Voltage	51	-0.5 to V _{CC} + 0.5	V
I _{IKC}	DC Input Diode Current on control pin (\	/ _{IN} < 0V)	- 50	mA
I _{IK}	DC Input Diode Current (V _{IN} < 0V)	± 50	mA	
I _{OK}	DC Output Diode Current		± 20	mA
Io	DC Output Current		± 300	mA
I _{OP}	DC Output Current Peak (pulse at 1ms,	10% duty cycle)	± 500	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current		± 100	mA
P _D	Power Dissipation at T _a =70°C (1) QFN		1120	mW
		500	mW	
T _{stg}	Storage Temperature	-65 to 150	°C	
1,	Lead Temperature (10 sec)		300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions not implied.

Table 5: Recommended Operating Conditions

Symbol	Parameter		Value	Unit
V _{CC}	Supply Voltage (note 1)	1.65 to 4.3	V	
V _I	Input Voltage		0 to V _{CC}	V
V _{IC}	Control Input Voltage	0 to 4.3	V	
Vo	Output Voltage		0 to V _{CC}	V
T _{op}	Operating Temperature		-55 to 125	°C
Input Rise and Fall Time Control In		V _{CC} = 1.65V to 2.7V	0 to 20	ns/V
ul/uv		$V_{CC} = 3.0 \text{V to } 4.3 \text{V}$	0 to 10	115/ V

¹⁾ Truth Table guaranteed: 1.2V to 4.3V.

⁽¹⁾ Derate above 70°C: by 18.5mW/°C for QFN package; by 5.6mW/°C for TSSOP.

Table 6: DC Specifications

		Test	Conditions				Value				
Symbol	Parameter	V _{cc}		Т	A = 25°	С	-40 to	85°C	-55 to	125°C	Unit
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V _{IH}	High Level	1.65-1.95		0.65V _{CC}			0.65V _{CC}		0.65V _{CC}		
	Input Voltage	2.3-2.5		1.4			1.4		1.4		
		2.7-3.0		1.4			1.4		1.4		V
		3.3		1.5			1.5		1.5		\ \
		3.6		1.7			1.7		1.7		
		4.3		2.2			2.2		2.2		4
V _{IL}	Low Level	1.65-1.95				0.40		0.40		0.40	1 C
	Input Voltage	2.3-2.5				0.50		0.50		0.50	
		2.7-3.0				0.50		0.50	1	0.50	1
		3.3				0.50		0.50		0.50	V
		3.6				0.50		0.50	*O	0.50	1
		4.3				1.3		1.3)\~	1.3	1
R _{ON}	Switch ON	4.3			0.40	0.50		0.60			
· JOIN	Resistance	3.0			0.40	0.50	3	0.60			1
	(1) 2.7 2.3 1.8	V _S =0V to V _{CC}		0.40	0.50	76	0.60			1	
			I _S =100mA		0.50	0.80	0)	0.80			Ω
			.5		0.70	3.0		4.0			1
		1.65			0.80	3.0		4.0			1
ΔR _{ON}	ON Resistance Match between channels (1,2)	2.7	V _S =1.5V I _S =100mA	(6)	0.06						Ω
R _{FLAT}	ON	4.3	.00								
	Resistance	3.0	V _S =1.5V								
	FLATNESS	2.7	I _S =100mA		0.07	0.15		0.15			1
	(3)	2.3									Ω
	0/6	1.65	V _S =0.8V I _S =100mA								
I _{OFF}	OFF State Leakage Current (nSn), (Dn)	4.3	V _S =0.3 or 4V			±10		± 100			nA
I _{IN}	Input Leakage Current	0 - 4.3	V _{IN} = 0 to 4.3V			±0.1		± 1			μА
I _{CC}	Quiescent Supply Current (1)	1.65-4.3	V _{IN} =V _{CC} or GND			±0.05		±0.2		±1	μА

Note 1: Guaranteed by design Note 2: $\Delta R_{ON} = R_{ON(MAX)} - R_{ON(MIN)}$. Note 3: Flatness is defined as the difference between the maximum and minimum value of on-resistance as measured over the specified analog signal ranges.

Table 7: AC Electrical Characteristics (C_L = 35pF, R_L = 50 Ω , t_r = $t_f \le 5 ns$)

		Test Co	ondition				Value				
Symbol	Parameter	V _{CC}		T _A = 25°C -40			-40 to	0 to 85°C -55 to 125°C			Unit
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
t _{PLH} , t _{PHL}	Propagation Delay	1.65-1.95			0.45						
,		2.3-2.7	V _I =OPEN		0.40						20
		3.0-3.6	VIOFEN		0.30						ns
		3.6-4.3			0.30						
t _{ON}	TURN-ON time	1.65-1.95	V _S =0.8V		70						
		2.3-2.7			30	50		60			nc -
		3.0-3.6 V _S =1.5V		30	50		60			ns	
		3.6-4.3			30	50		60			
t _{OFF}	TURN-OFF time	1.65-1.95	V _S =0.8V		45						
		2.3-2.7			25	30		40), —	ns
		3.0-3.6	V _S =1.5V		25	30		40			110
		3.6-4.3			25	30		40			
	Break Before Make	1.65-1.95	C _L =35pF				Y.C				
t _D	Time Delay	2.3-2.7	$R_L = 50\Omega$	2	15						ns
ď		3.0-3.6	V _S =1.5V	2	15)				113
		3.6-4.3	V5-1.0V	2	15						
Q	Charge injection	1.65-1.95	C _L = 100pF		50						
		2.3-2.7	$R_L = 1M\Omega$		40						рС
		3.0-3.6	V _{GEN} = 0V		35						ρО
		3.6-4.3	$R_{GEN} = 0\Omega$		35						

Table 8: Analog Switch Characteristics (C_L = 5pF, R_L = 50 Ω , T_A = 25°C)

		Te	st Condition				Value				
Symbol	Parameter	V _{CC}		Т	_A = 25°	С	-40 to	85°C	-55 to	125°C	Unit
	*6	(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
OIRR	Off Isolation (1)	1.65-4.3	V _S = 1V _{RMS} f= 100KHz		-64						dB
Xtalk	Crosstalk	1.65-4.3	V _S = 1V _{RMS} f= 100KHz		-54						dB
THD	Total Harmonic Distortion	2.3-4.3	$R_L = 600\Omega$ $V_{IN} = 2V_{PP}$ f = 20Hz to $20kHz$		0.03						%
BW	-3dB Bandwidth	1.65-4.3	$R_L = 50\Omega$		50						MHz
C _{IN}	Control Pin Input Capacitance				5						
C _{Sn}	Sn Port Capaci- tance	3.3	f= 1MHz		37						pF
C _D	D Port Capaci- tance when Switch is Enabled	3.3	f= 1MHz		84						

Note 1: Off Isolation = 20Log_{10} ($\text{V}_{\text{D}}\text{/V}_{\text{S}}$), V_{D} = output. V_{S} = input to off switch

Figure 3: On Resistance

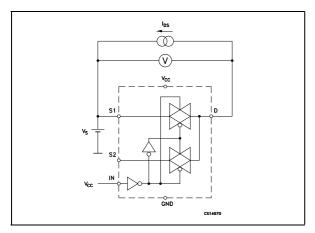


Figure 4: Off Leakage

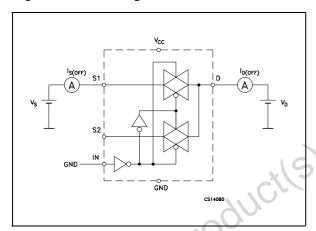


Figure 5: Off Isolation

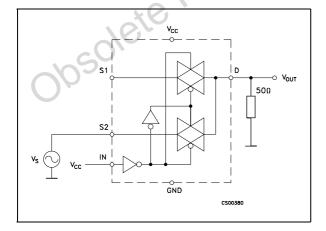


Figure 6: Bandwidth

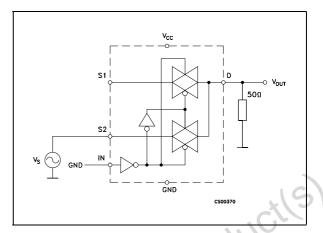


Figure 7: Channel To Channel Crosstalk

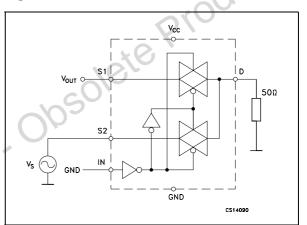
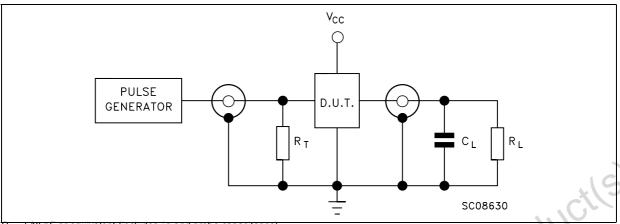


Figure 8: Test Circuit



 $c_L = 5/35 pF$ or equivalent (includes jig and probe capacitance) $R_L = 50\Omega$ or equivalent $R_T = Z_{OUT}$ of pulse generator (typically $50\Omega)$

Figure 9: Break Before Make Time Delay

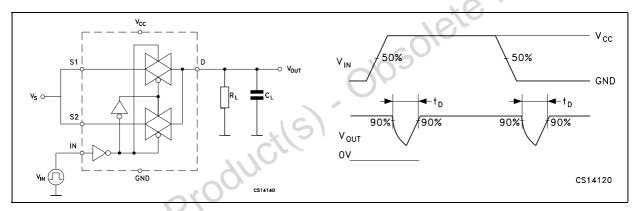


Figure 10: Charge Injection (V_{GEN} =0V, R_{GEN} =0 Ω , R_L =1 $M\Omega$, C_L =100pF)

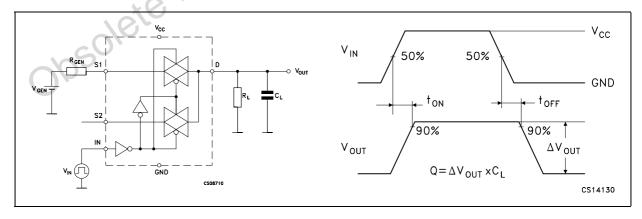
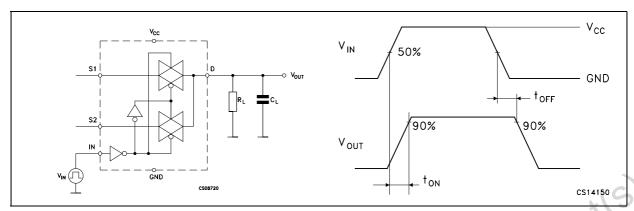


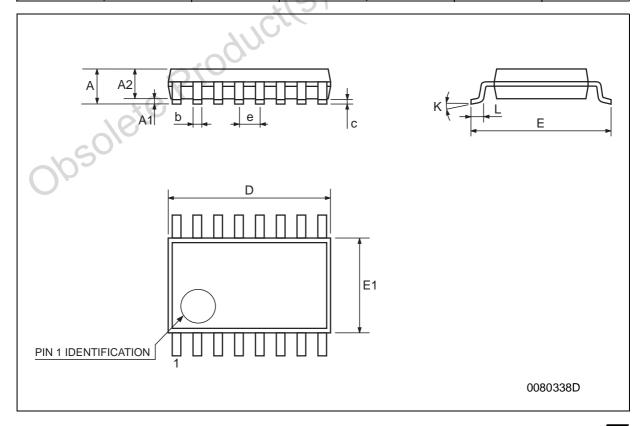
Figure 11: Turn On, Turn Off Delay Time



Obsolete Product(s).

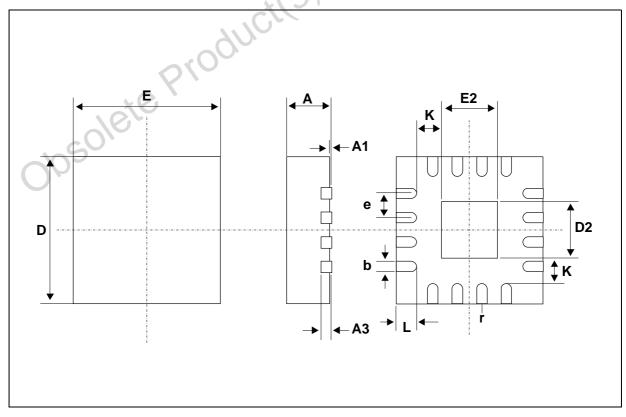
TSSOP16 MECHANICAL DATA

DIM		mm.			inch	
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
А			1.2			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.8	1	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
С	0.09		0.20	0.004		0.0079
D	4.9	5	5.1	0.193	0.197	0.201
E	6.2	6.4	6.6	0.244	0.252	0.260
E1	4.3	4.4	4.48	0.169	0.173	0.176
е		0.65 BSC		120°	0.0256 BSC	
К	0°		8°	0°		8°
L	0.45	0.60	0.75	0.018	0.024	0.030



QFN16 (3x3) MECHANICAL DATA

DIM.		mm.		inch			
DIWI.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.	
А	0.80	0.90	1.00	0.032	0.035	0.039	
A1		0.02	0.05		0.001	0.002	
А3		0.20			0.008	4	
b	0.18	0.25	0.30	0.007	0.010	0.012	
D		3.00			0.118	(C)	
D2	1.55	1.70	1.80	0.061	0.067	0.071	
E		3.00			0.118	,	
E2	1.55	1.70	1.80	0.061	0.067	0.071	
е		0.50		7/6	0.020		
K		0.20		MS	0.008		
L	0.30	0.40	0.50	0.012	0.016	0.020	
r	0.09		16)	0.006			





Tape & Reel TSSOP16 MECHANICAL DATA

DIM		mm.			inch	
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
А			330			12.992
С	12.8		13.2	0.504		0.519
D	20.2			0.795		
N	60			2.362		1.0
Т			22.4			0.882
Ao	6.7		6.9	0.264		0.272
Во	5.3		5.5	0.209	ArC	0.217
Ko	1.6		1.8	0.063		0.071
Po	3.9		4.1	0.153	10	0.161
Р	7.9		8.1	0.311	7	0.319

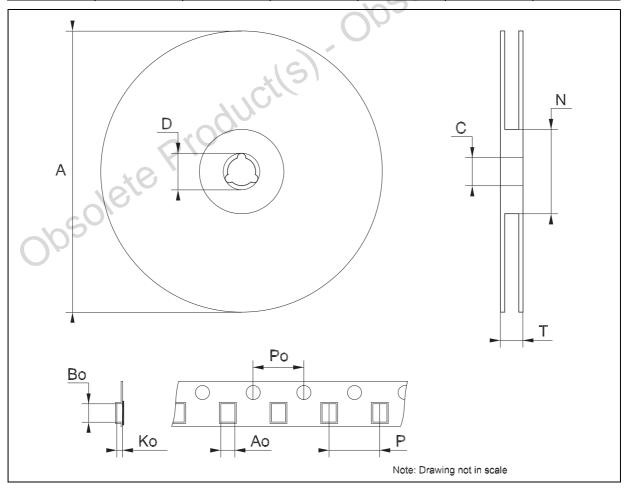


Table 9: Revision History

Date	Revision	Description of Changes
14-May-2004	3	Characteristics at V _{CC} = 4.3 V Added on Tables 3, 4, 5, 6 and 7.
01-Jun-2004	4	ESD Performance (Analog Channels) added on top page.
04-Jul-2005	5	The Q Values on Table 7 has been updated.

Obsolete Product(s). Obsolete Product(s)



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